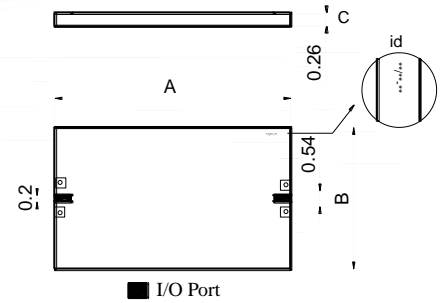


Thin Film ceramic Filter

BMBP20R75/3R7-6DA

Precautions

1. The chip is recommended sub-cavity use, both sides of the side wall from about 0.2mm, surface distance Cover about 3mm, the chip ports are interchangeable;
2. Chip recommended low-stress conductive adhesive (such as ME8456) bonding;
3. Chip should be installed in Kovar (recommended) or molybdenum copper with ceramic thermal expansion coefficient(6.7ppm / °C) on the carrier, the carrier thickness $\geq 0.2\text{mm}$;
- 4 circuit board micro-chip wire bonding connection, it is recommended microstrip bonding at mining T-type structure to match, T-size as right



| Circuit boardRogers 5880 , 10mil | Circuit boardRogers 4350, 10mi l |
|--------------------------------------|----------------------------------|
| | |
| frequency: DC-38GHz | frequency: DC-32GHz |
| 注: T 型图形顶端基板白边 50um; 频率 10GHz 以下无需匹配 | |

Features

| |
|---|
| high-precision film processing technology |
| high performance, low temperature drift, high power |
| Ceramic substrate, 50Ω coplanar waveguide output |
| Gold wire bonding, suitable for multi-chip integrated module applications |

Environmental parameters

| | |
|---------------------|--------------|
| Working temperature | -55°C~+85°C |
| storage temperature | -55°C~+125°C |
| Maximum input power | 35dBm |

Electrical Specifications

| | |
|--------------------------------|--|
| Center frequency(f0) | 20.75 |
| Passband frequency range (GHz) | 18.9-22.6 |
| Band fluctuations (dB) | 1 |
| Center insertion loss (dB) | 2 |
| Return loss (dB) | 15 |
| Band attenuation (dB) | $\geq 40@15.3\text{GHz}$ $\geq 40@24.5\text{GHz}$ |

